

MECGaNC30

4 to 6 GHz GaN HEMT Power Amplifier



Product Description

MECGaNC30 is a GaN HEMT based High Power Amplifier designed by MEC for C-Band applications and fabricated on 0.25 μ m GaN on SiC process.

The MECGaNC30 provides more than 30W of saturated output power in the frequency range from 4.1 GHz to 5.9 GHz with a PAE higher than 37% and 27 dB of small signal Gain. Operating in the reduced range from 4.6 GHz to 5.8 GHz it reaches an output Power from 35W to 40W.

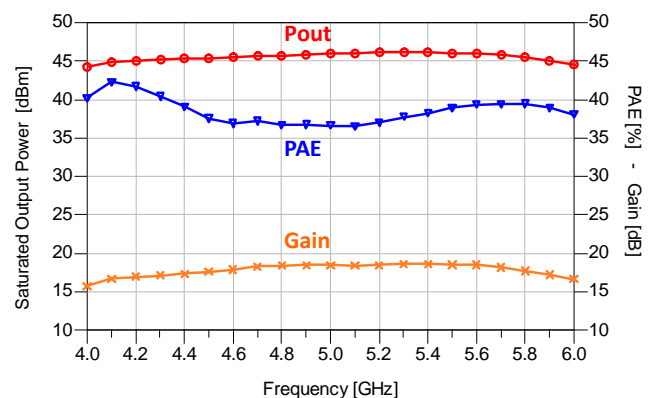
The MECGaNC30 is fully matched to 50 Ω with DC decoupling capacitors on both Input and Output ports. Bond Pad are gold plated for compatibility with thermo-compression bonding process.

Main Features

- 0.25 μ m GaN HEMT Technology
- 4.1 – 5.9 GHz full performances Frequency Range
- 30W Output Power @ Pin 27.5 dBm
- 37% PAE @ Pin 27.5 dBm
- 30% PAE @ Pout 20 Watt
- 27 dB Small Signal Gain
- Bias: Vd = 28V, Id = 1A, Vg = -3V (Typ.)
- Chip Size: 5.5 x 3.8 x 0.1 mm

Applications

- Radar
- Telecom
- Test Instrumentation



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Main Characteristics

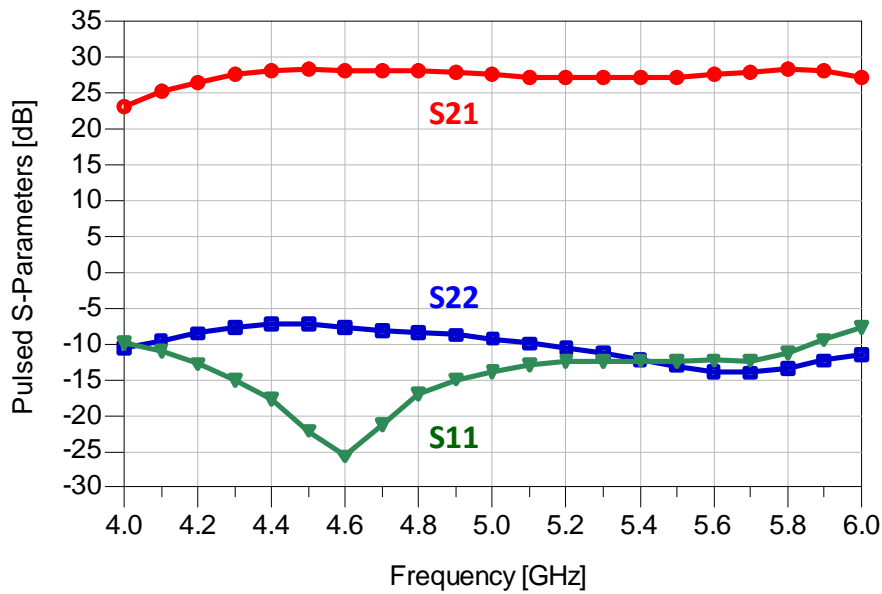
Test Conditions: $T_{\text{base_plate}} = 25^{\circ}\text{C}$, $V_d = 28\text{ V}$, $I_{dq} = 1\text{ A}$, Pulse Width = 50 μs , Duty Cycle = 15%

Parameter	Min	Typ	Max	Unit
Operating frequency	4.1	5	5.9	GHz
Small Signal Gain	25	27	28	dB
Input Return Loss	10	13		dB
Output Return Loss	7	10		dB
Saturated Output Power	45		46	dBm
Power Added Efficiency	37		42	%
Power Added Efficiency @ $P_{\text{out}} = 20\text{ Watt}$	30		37	%
Saturated Output Power @ [4.6 – 5.8] GHz	45		46	dBm
Drain Supply Voltage	25	28	30	V
Supply Quiescent Drain Current		1		A
Supply Drain Current	2.5		3.8	A
Gate Voltage		-3		V

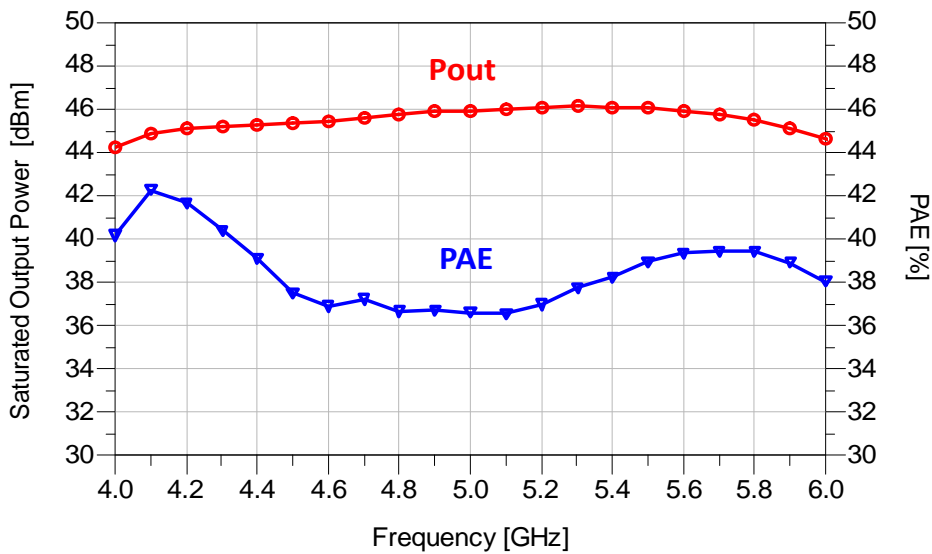
* Performances described in this document are based on preliminary on-jig characterization.
More details and new parameter will be carried out by the ongoing test campaign.

Typical Measured Performances

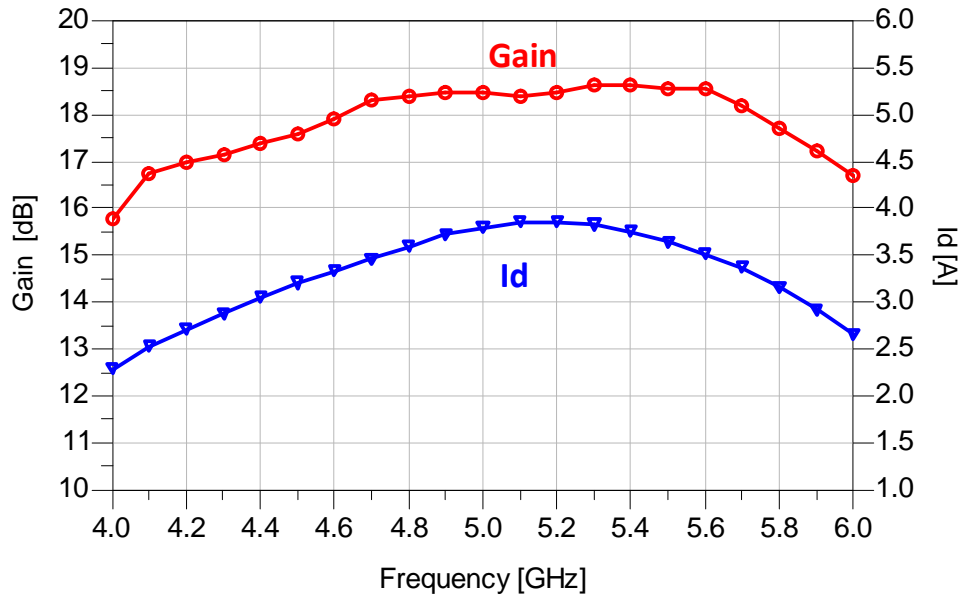
Linear Gain (S21), Input (S11) and Output (S22) Reflection Coefficients Vs. Frequency



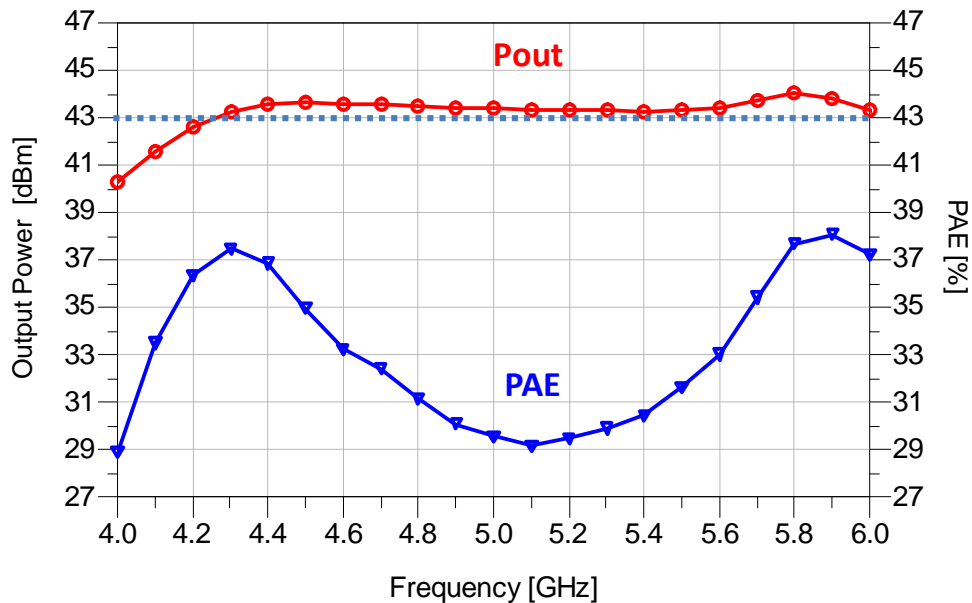
Output Power and PAE @ Pin = 27.5 dBm Vs. Frequency



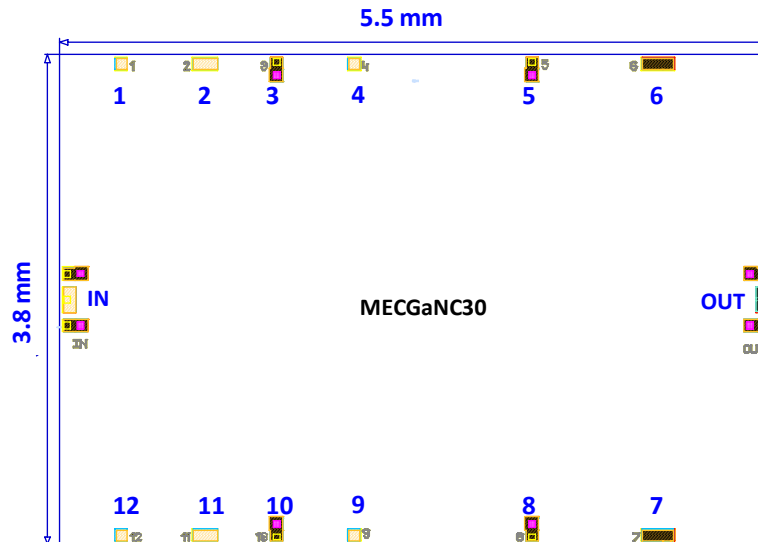
Gain and Drain Current @ Pin = 27.5 dBm Vs. Frequency



Output Power and PAE @ Pin = 19.5 dBm Vs. Frequency



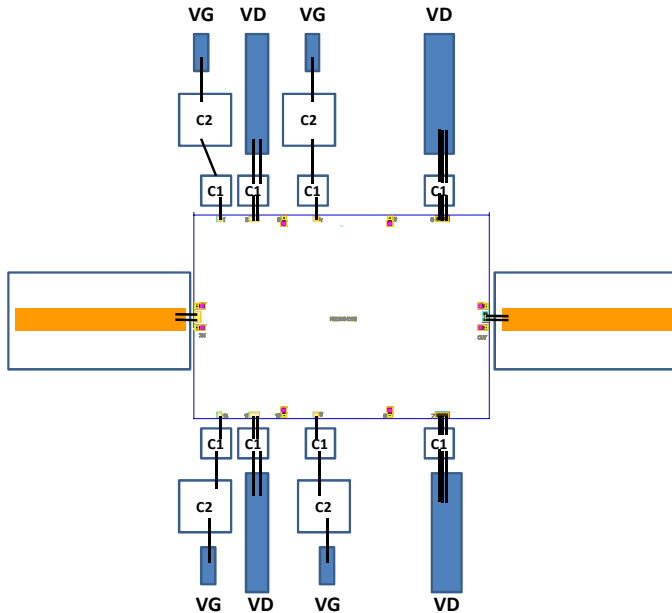
Bond Pad Configuration



- A tolerance of $\pm 35\mu\text{m}$ has to be considered for chip dimensions
- Chip Thickness is $100\ \mu\text{m} \pm 10\ \mu\text{m}$
- RF Pads [IN, OUT] = $100\mu\text{m} \times 200\mu\text{m}$
- DC Pads [1, 3, 4, 5, 8, 9, 10, 12] = $100\mu\text{m} \times 100\mu\text{m}$
- DC Pads [2, 11] = $200\mu\text{m} \times 100\mu\text{m}$
- DC Pads [6, 7] = $250\mu\text{m} \times 100\mu\text{m}$

Bond Pad #	Symbol	Description
IN	RFin	Input RF Port
OUT	RFout	Output RF Port
1, 4, 9, 12	Vg	Gate Negative Supply Voltage
2, 6, 7, 11	Vd	Drain Positive Supply Voltage
3, 5, 8, 10	GND	Ground Pads – Not Connected

Assembly Recommendations



Bond Pad #	Connection	External Components
IN and OUT	2 Bonding Wires $L_{\text{bond}} = 0.3\text{nH}$	
1, 4, 9, 12 - Vg	$L_{\text{bond}} \leq 1\text{nH}$	C1 = 100pF/10V C2 = 10nF/10V
2, 11 - Vd	2 Bonding Wires $L_{\text{bond}} \leq 1\text{nH}$	Pulsed mode C1 = 100pF/50V
6, 7 - Vd	3 Bonding Wires $L_{\text{bond}} \leq 1\text{nH}$	CW mode: C1 = 100pF/50V C2 = 10nF/50V

- Eutectic Die bond using AuSn (80/20) solder is recommended.
- Great care must be used for thermal dimensioning.
- The backside of the die is the Source (ground) contact.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.

Bias Procedure

Bias-Up

1. Vg set to -5 V.
2. Vd set to +28 V.
3. Adjust Vg until quiescent Id is 1 A
(Vg = -3.0 V Typical).
4. Apply RF signal.

Bias-Down

1. Turn off RF signal.
2. Reduce Vg to -5 V ($I_{d0} \approx 0\text{ mA}$).
3. Set Vd to 0 V.
4. Set Vg to 0 V.

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Notice

The furnished information is believed to be reliable. However, performances and specifications contained herein are based on preliminary characterizations and then susceptible to possible variations. On the basis of customer requirements the product can be tested and characterized in specific operating conditions and, if needed, tuned to meet custom specifications.